L Number	Hits	Search Text	DB	Time stamp
1	569	"buried strap" (bottle adj1 trenches)	USPAT;	2004/06/12 09:23
		(bottle adj1 trench)	US-PGPUB;	
			EPO; JPO	
2	63	("buried strap" (bottle adj1 trenches)	USPAT;	2004/06/12 09:23
		(bottle adj1 trench)) adj3 (remov\$3	US-PGPUB;	
	40000	etch\$3)	EPO; JPO	
-	12772	438/199.ccls. 438/200.ccls. 438/230.ccls.	USPAT;	2004/06/12 09:22
		438/239.ccls. 438/243.ccls. 438/270.ccls. 438/444.ccls. 438/445.ccls. 438/446.ccls.	US-PGPUB; EPO; JPO	
		438/696.ccls. 438/697.ccls. 438/700.ccls.	EPO, OPO	
		438/704.ccls. 438/706.ccls. 438/745.ccls.		
		438/748.ccls. 438/754.ccls. 257/301.ccls.		
		257/532.ccls. 257/204.ccls. 257/277.ccls.		
		257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.		
-	4797	(438/199.ccls. 438/200.ccls. 438/230.ccls.	USPAT;	2004/06/02 15:12
		438/239.ccls. 438/243.ccls. 438/270.ccls.	US-PGPUB;	
		438/444.ccls. 438/445.ccls. 438/446.ccls.	EPO; JPO	
		438/696.ccls. 438/697.ccls. 438/700.ccls. 438/704.ccls. 438/706.ccls. 438/745.ccls.		
		438/748.ccls. 438/754.ccls. 257/301.ccls.		
		257/532.ccls. 257/204.ccls. 257/277.ccls.		ł
		257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
1		SiN)	1	
-	4483	((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:13
		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls. 438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
		SiN)) and ("silicon oxide" oxide sio2)		
-	4297	. , , ,	USPAT;	2004/06/02 15:13
		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls. 438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		1
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		1
		SiN)) and ("silicon oxide" oxide sio2))		
		and etch\$3		0004/06/00 15 15
-	2780	((((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:13
		438/230.ccls. 438/239.ccls. 438/243.ccls. 438/270.ccls. 438/444.ccls. 438/445.ccls.	US-PGPUB; EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.	EFO, OFO	
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
		Sin)) and ("silicon oxide" oxide sio2))		
_	403	and etch\$3) and polysilicon ((((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:14
-	403	438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	2004/00/02 15:14
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
		SiN)) and ("silicon oxide" oxide sio2)) and etch\$3) and pmos		
	L <u>.</u>	and ecentral and pinos	L	1

	1.501	1420/100 1- 420/000 1 420/020		0004/06/00 45 4
-	1501	(438/199.ccls. 438/200.ccls. 438/230.ccls.	USPAT;	2004/06/02 15:14
		438/239.ccls. 438/243.ccls. 438/270.ccls.	US-PGPUB;	
		438/444.ccls. 438/445.ccls. 438/446.ccls.	EPO; JPO	
		438/696.ccls. 438/697.ccls. 438/700.ccls.		
		438/704.ccls. 438/706.ccls. 438/745.ccls.		
		438/748.ccls. 438/754.ccls. 257/301.ccls.		
		257/532.ccls. 257/204.ccls. 257/277.ccls.		
		257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and (void voids		
		residue)		
-	761	(((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:14
		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
		SiN)) and ("silicon oxide" oxide sio2))		
		and (voids void residue)		
-	0	((((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:14
		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
		SiN)) and ("silicon oxide" oxide sio2))		
		and (voids void residue)) and salient		
-	48	((((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:22
1		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"		
		SiN)) and ("silicon oxide" oxide sio2))		
		and (voids void residue)) and (protru\$4)		
-	1948	salient and semiconductor	USPAT;	2004/06/02 15:23
			US-PGPUB;	
			EPO; JPO	0001/06/00 15
-	324	(salient and semiconductor) and ("silicon	USPAT;	2004/06/02 15:23
1		nitride" sin)	US-PGPUB;	
			EPO; JPO	
-	240	((salient and semiconductor) and ("silicon	USPAT;	2004/06/02 15:28
		nitride" sin)) and ("silicon oxide" oxide	US-PGPUB;	
		sio2)	EPO; JPO	
-	438	((((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 15:29
		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	•
1		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.	-	
	1	257/301.ccls. 257/532.ccls. 257/204.ccls.		
	1	257/277.ccls. 257/516.ccls. 438/245.ccls.		
	1	438/386-388.ccls.) and ("silicon nitride"		
	[SiN)) and ("silicon oxide" oxide sio2))		
L		and (voids void residue)) and polysilicon		<u> </u>

-	274	(((((438/199.ccls. 438/200.ccls.	USPAT;	2004/06/02 16:17
		438/230.ccls. 438/239.ccls. 438/243.ccls.	US-PGPUB;	
		438/270.ccls. 438/444.ccls. 438/445.ccls.	EPO; JPO	
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.	,	1
		438/745.ccls. 438/748.ccls. 438/754.ccls.		1
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"]
		SiN)) and ("silicon oxide" oxide sio2))		
		and (voids void residue)) and polysilicon)		
	Ī	and sidewall\$1] ;
_	2047	(sidewalls sidewall "insulation collar")	USPAT;	2004/06/02 16:17
	2047	near3 ("silicon nitride" SiN)	US-PGPUB;	2004/00/02 10:1/
		Meals (Silicon Miclide Sin)	EPO; JPO]
	591	((sidewalls sidewall "insulation collar")	USPAT;	2004/06/02 16:18
_	291	near3 ("silicon nitride" SiN)) same	US-PGPUB;	2004/06/02 16:18
		(portion part protruding protrusion	EPO; JPO	
		residue remainder)		
_	559	, , , == == = = = = = = = = = = = = =	USPAT;	2004/06/02 16:19
		near3 ("silicon nitride" SiN)) same	US-PGPUB;	
		(portion part protruding protrusion	EPO; JPO	
		residue remainder)) and etch\$3	i	
-	545		USPAT;	2004/06/02 16:19
		collar") near3 ("silicon nitride" SiN))	US-PGPUB;	
		same (portion part protruding protrusion	EPO; JPO	
		residue remainder)) and etch\$3) not		
		((((((438/199.ccls. 438/200.ccls.		
		438/230.ccls. 438/239.ccls. 438/243.ccls.		
		438/270.ccls. 438/444.ccls. 438/445.ccls.		
		438/446.ccls. 438/696.ccls. 438/697.ccls.		
		438/700.ccls. 438/704.ccls. 438/706.ccls.		
		438/745.ccls. 438/748.ccls. 438/754.ccls.		
		257/301.ccls. 257/532.ccls. 257/204.ccls.		
		257/277.ccls. 257/516.ccls. 438/245.ccls.		
		438/386-388.ccls.) and ("silicon nitride"]
		SiN)) and ("silicon oxide" oxide sio2))		
		and (voids void residue)) and polysilicon)		
		and sidewall\$1)		
_	569		USPAT;	2004/06/12 09:23
		(bottle adj1 trench)	US-PGPUB;	
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	EPO; JPO	1
_	1	5244843.pn.	USPAT	2004/06/12 08:51
_	1	_	USPAT	2004/06/12 08:51
		1	1	